In the Specification:

Please amendment paragraph [0023] as follows:

[0023] FIG. 2 is a simplified diagram of an EUV lithography system 200 in accordance with one embodiment of the present invention. The dimensions of various components are exaggerated to better illustrate the components of this embodiment. As shown, the EUV lithography system 200 includes an illuminator chamber (not shown), a mask or reticle chamber 204 and a projection optics chamber 209 which containins contains the projection optics 206 and a wafer stage 208. Although not shown, the illuminator chamber houses a laser-produced or discharge-produced plasma source and the illumination system.